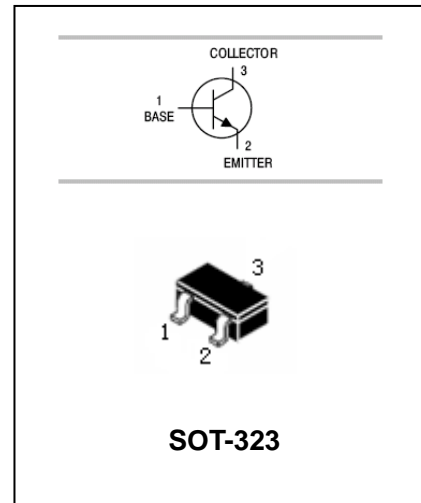


NPN General Purpose Transistor

MMST5551

FEATURES

- Epitaxial planar die construction.
- Complementary PNP type available (MMST5401).
- Also available in lead free version.



APPLICATIONS

- Ideal for medium power amplification and switching.

ORDERING INFORMATION

Type No.	Marking	Package Code
MMST5551	K4N	SOT-323

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	UNIT
V _{CBO}	collector-base voltage	180	V
V _{CEO}	collector-emitter voltage	160	V
V _{EBO}	emitter-base voltage	6	V
I _C	collector current (DC)	0.6	A
P _C	Collector dissipation	0.3	W
R _{θJA}	Thermal resistance junction to ambient	625	°C/W
T _j , T _{stg}	junction and storage temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

NPN General Purpose Transistor

MMST5551

Symbol	Parameter	Test conditions	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu A, I_E=0$	180		
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=0.1mA, I_B=0$	160		
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10\mu A, I_C=0$	6		
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 120V$	-	50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 4V$	-	50	nA
h_{FE}	DC current gain	$V_{CE} = 5V; I_C = 1mA$ $V_{CE} = 5V; I_C = 10mA$ $V_{CE} = 5V; I_C = 50mA$	80 80 30	- 250 -	
$V_{CE(sat)}$	collector-emitter saturation voltage	$I_C = 50mA; I_B = 5mA$ $I_C = 10mA; I_B = 1mA$	-	0.2 0.15	V
$V_{BE(sat)}$	base-emitter saturation voltage	$I_C = 50mA; I_B = 5mA$ $I_C = 10mA; I_B = 1mA$	-	1 1	V
f_T	transition frequency	$I_C = 10mA; V_{CE} = 10V;$ $f = 100MHz$	80	-	MHz

TYPICAL CHARACTERISTICS @ $T_a=25^\circ C$ unless otherwise specified

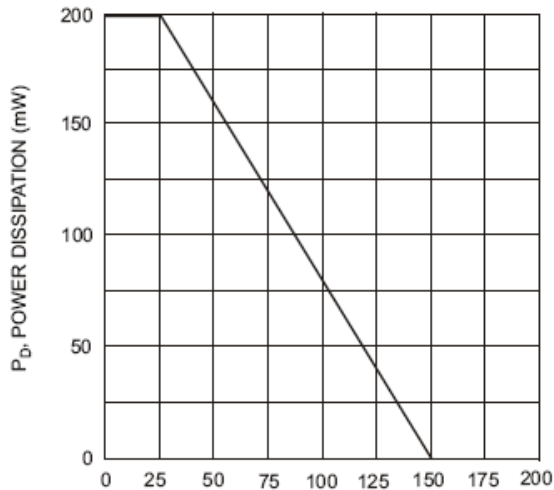


Fig. 1, Max Power Dissipation vs Ambient Temperature

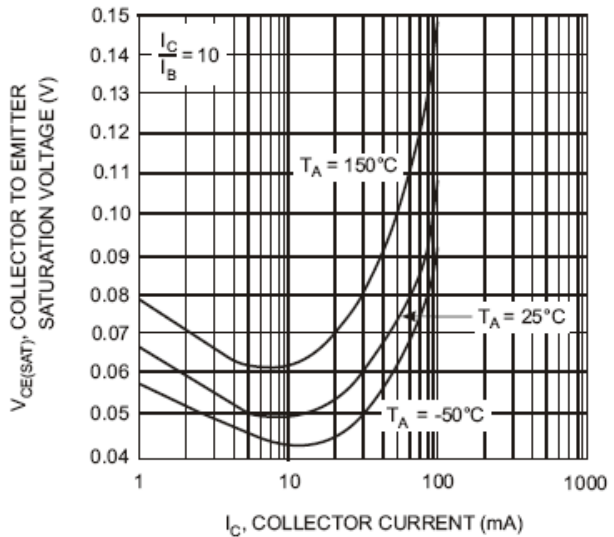


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

NPN General Purpose Transistor

MMST5551

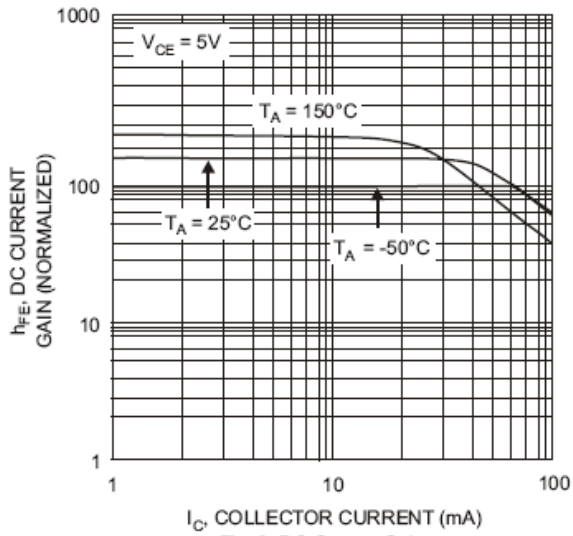


Fig. 3, DC Current Gain vs Collector Current

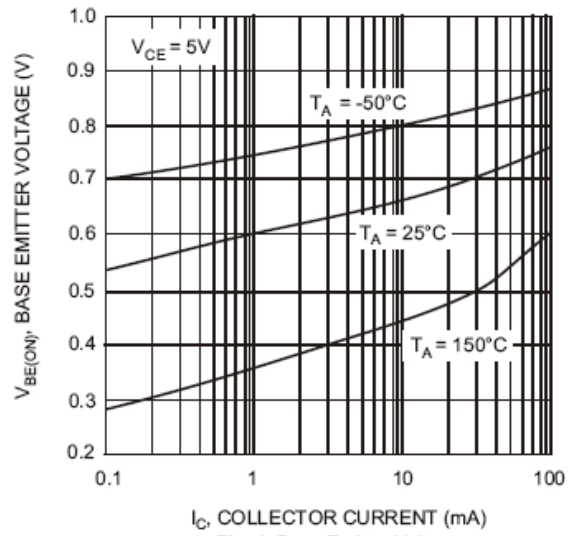


Fig. 4, Base Emitter Voltage vs. Collector Current

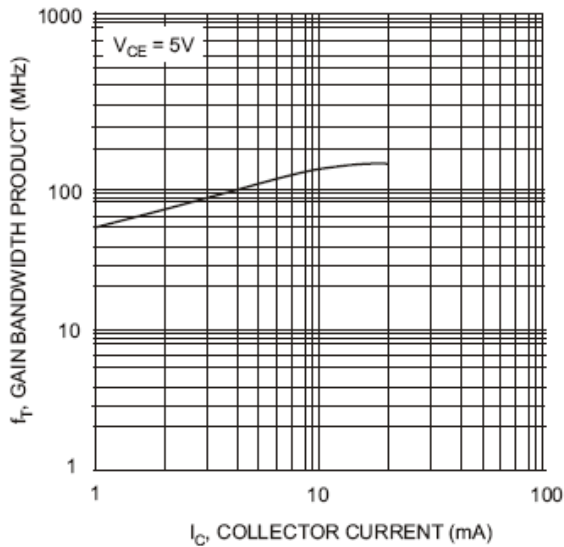


Fig. 5, Gain Bandwidth Product vs. Collector Current

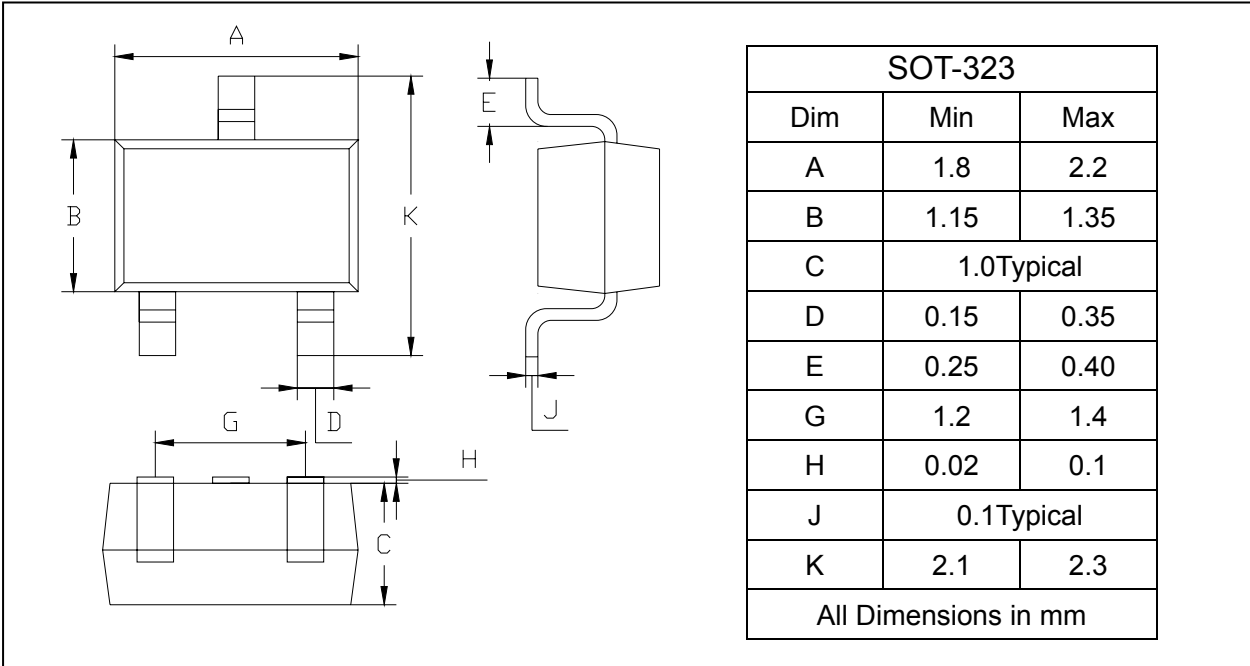
NPN General Purpose Transistor

MMST5551

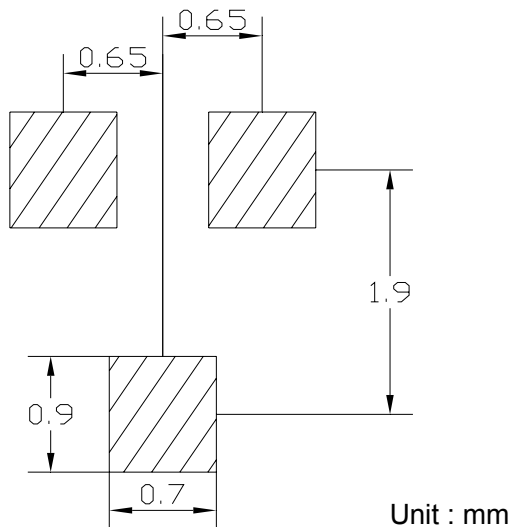
PACKAGE OUTLINE

Plastic surface mounted package

SOT-323



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
MMST5551	SOT-323	3000/Tape&Reel

www.s-manuals.com